

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	24211	(MRAM MTJ (magnetic near resistor) magnetoresist\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/22 14:40
L2	1	1 and (((digit write) near line\$1) (conductive near (layer film))) near (beneath below underneath) near (magnetic near resistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/22 14:24
L3	3	1 and ((beneath below underneath) near (magnetic near resistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/22 14:18
L4	4061	1 and (((digit write) near line\$1) (conductive near (layer film)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/22 14:17
L5	2861	4 and (beneath below underneath overlap\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/22 14:19
L6	3	4 and ((beneath below underneath overlap\$4) near2 resistor\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/22 14:23
L7	1	(((digit write) near line\$1) (conductive near (layer film))) near (beneath below underneath overlap\$4) near (magnetic near resistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/22 14:23
L8	3265	((beneath below underneath overlap\$4) near2 resistor\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/22 14:23
L9	129	8 and ((digit write conduct\$3) near line\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/22 14:24

L10	969	(magnetic near resistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/22 14:40
L11	131	10 and (MRAM MTJ magnetoresist\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/22 14:56
L12	0	(MRAM MTJ magnetoresist\$3) AND (memory near cell\$1) AND ((digit write) near line\$1) AND substrate AND (magnetic near resistor\$1) AND (beneath below underneath overlap\$4) AND (contact near (hole open\$3 via plug)) AND penetrat\$3 AND (between near (digit write) near line\$1).CLM.	US-PGPUB; USPAT	OR	ON	2005/09/22 15:03
L13	0	(MRAM MTJ magnetoresist\$3) AND (memory cell\$1) AND ((conduct\$3 digit write) near line\$1) AND substrate AND (magnetic near resistor\$1) AND (beneath below underneath overlap\$4) AND (contact near (hole open\$3 via plug)) AND penetrat\$3 AND (between near (digit write) near line\$1).CLM.	US-PGPUB; USPAT	OR	ON	2005/09/22 15:03
L14	0	(MRAM MTJ magnetoresist\$3) AND (memory cell\$1) AND ((conduct\$3 digit write) near line\$1) AND substrate AND (magnetic near resistor\$1) AND (beneath below underneath overlap\$4) AND (contact near (hole open\$3 via plug)) AND penetrat\$3 AND (between near (conduct\$3 digit write) near line\$1).CLM.	US-PGPUB; USPAT	OR	ON	2005/09/22 15:04
L15	0	(MRAM MTJ magnetoresist\$3) AND (memory cell\$1) AND ((first second) near (conduct\$3 digit write) near line\$1) AND substrate AND (magnetic near resistor\$1) AND (beneath below underneath overlap\$4) AND (contact near (hole open\$3 via plug)) AND penetrat\$3 AND (between near (conduct\$3 digit write) near line\$1).CLM.	US-PGPUB; USPAT	OR	ON	2005/09/22 15:05
L16	1	(MRAM MTJ magnetoresist\$3) AND (memory cell\$1) AND ((first second) near (conduct\$3 digit write) near line\$1) AND substrate AND (magnetic near resistor\$1) AND (beneath below underneath overlap\$4) AND (contact near (hole open\$3 via plug)) AND penetrat\$3 AND (between near2 (conduct\$3 digit write) near line\$1).CLM.	US-PGPUB; USPAT	OR	ON	2005/09/22 15:05